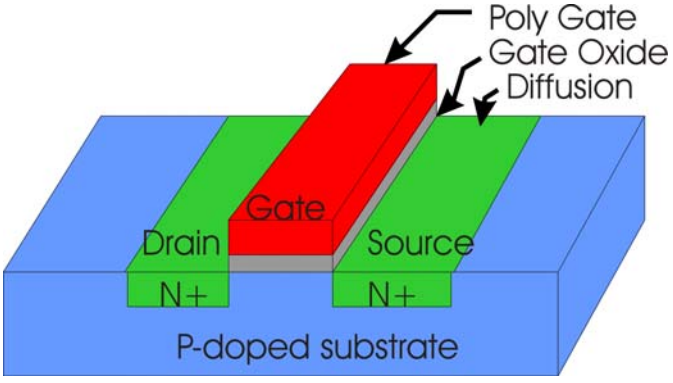
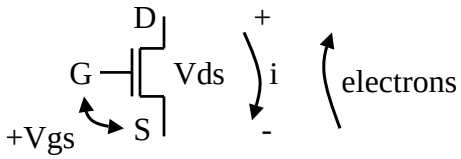
CS/EE 6710

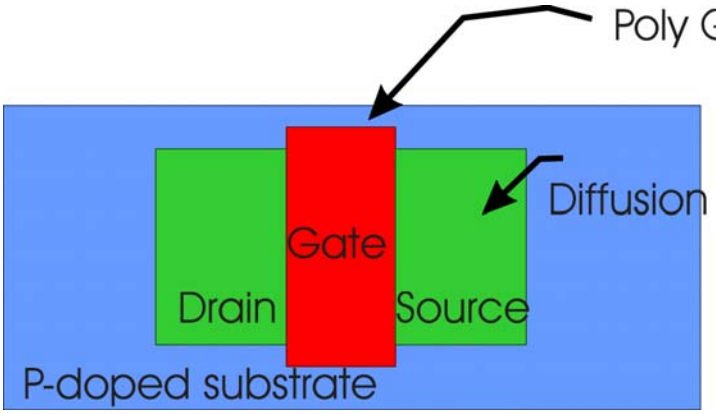
CMOS Processing

N-type Transistor



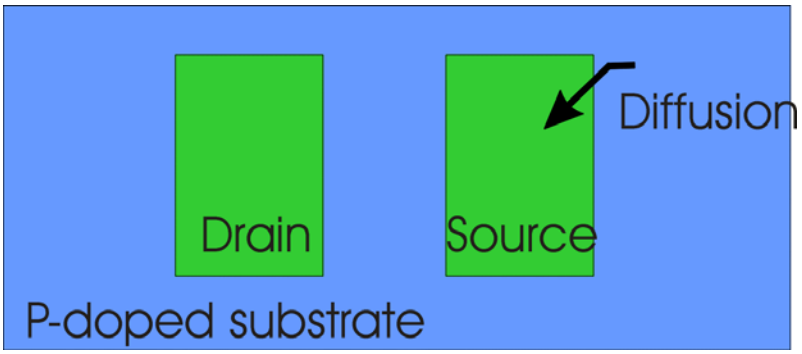


N-type from the top



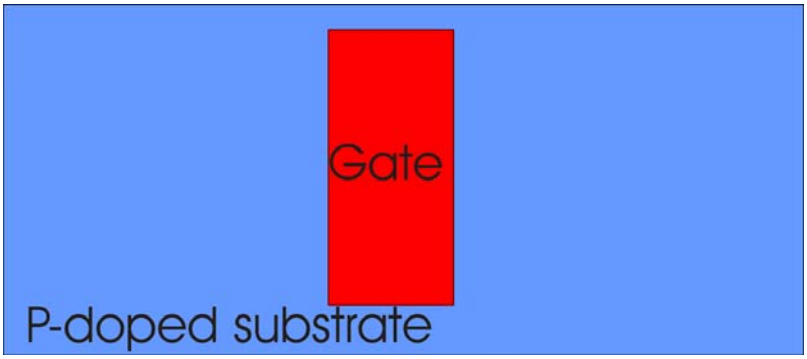
- Top view shows patterns that make up the transistor

Diffusion Mask



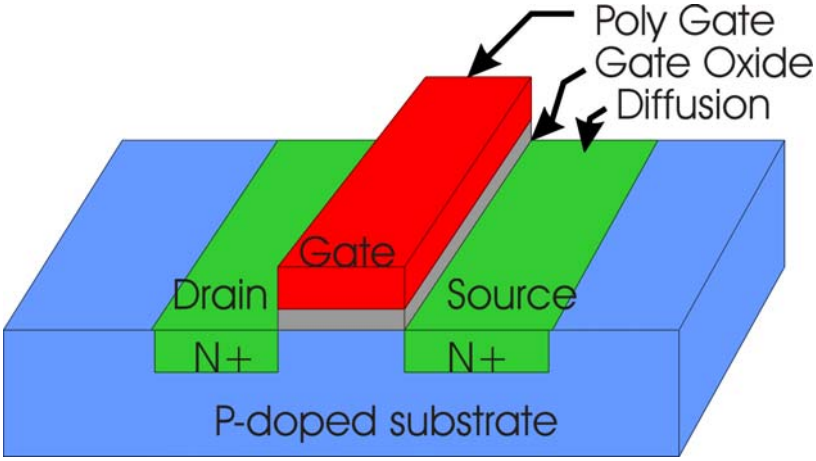
- Mask for just the diffused regions

Polysilicon Mask



- Mask for just the polysilicon areas

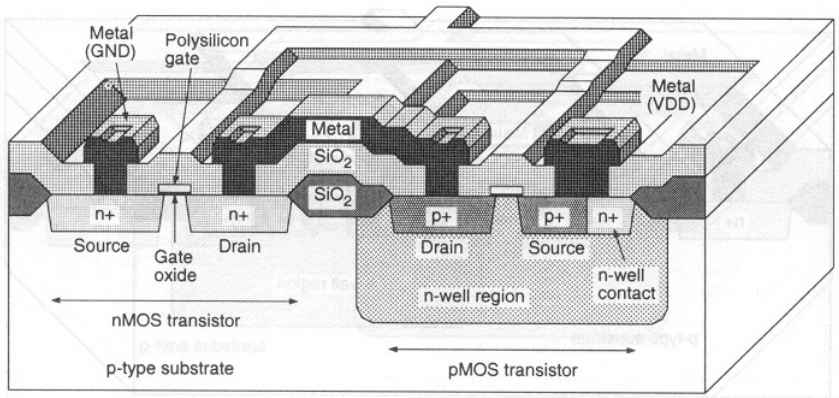
Combine the two masks



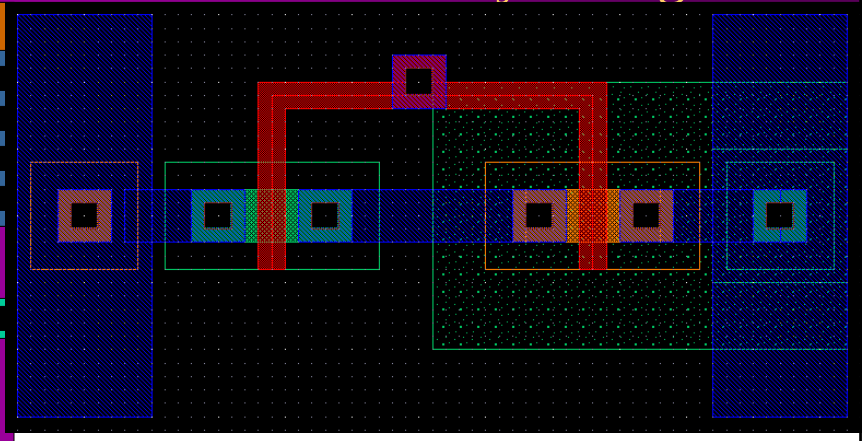
- You get an N-type transistor
  - There are other steps in the process…

A Cutaway View

- CMOS structure with both transistor types



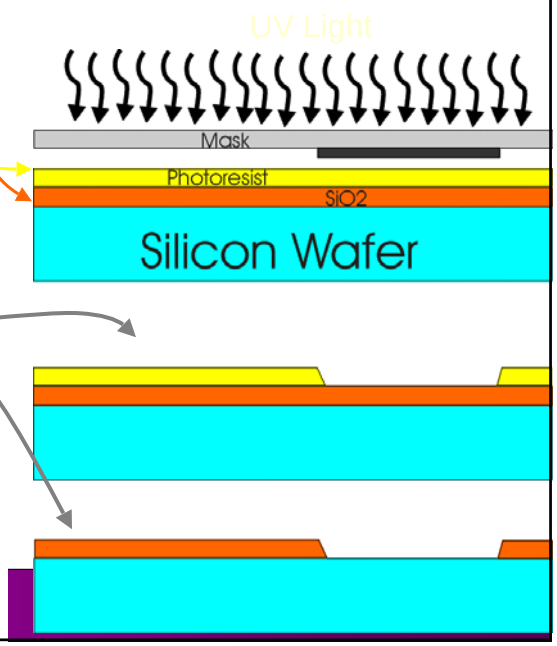
Look at Inverter Layout Again



- How many layers?
- How many processing steps?

Photolithography

- Oxidation Layer
- Photoresist (PR) Coating
- Stepper Exposure
- PR development and bake
- Acid Etching
- Spin, Rinse, Dry
- Processing step
- PR removal (ashing)

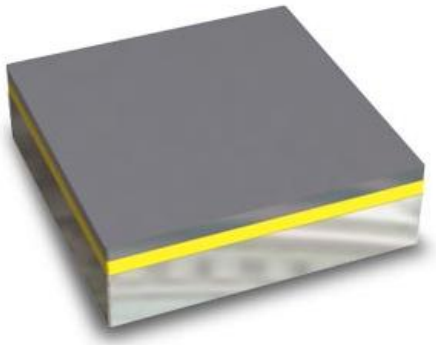


Photolithographic Process

The first step is to grow a very thin insulating layer of silicon dioxide (yellow layer) on the entire surface of the pure silicon wafer by exposing it to extreme heat in an atmosphere of pure oxygen.

forward

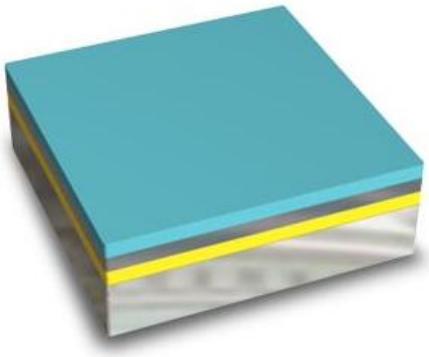
Photolithographic Process



Next, a thin layer of aluminum (gray layer) is applied by vacuum metallization directly on top of the silicon dioxide layer. This material will ultimately become the "silicon seascape".

back forward

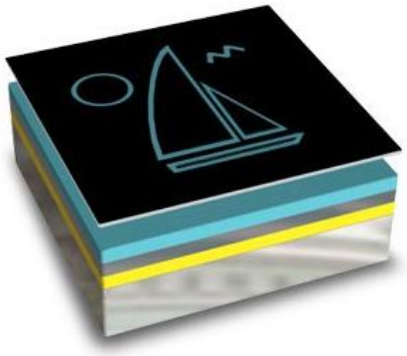
Photolithographic Process



A thin film of photoresist (blue layer) is applied to the surface of the entire wafer, which is then spun at high speed to evenly spread the viscous fluid–like photoresist across the surface.

back forward

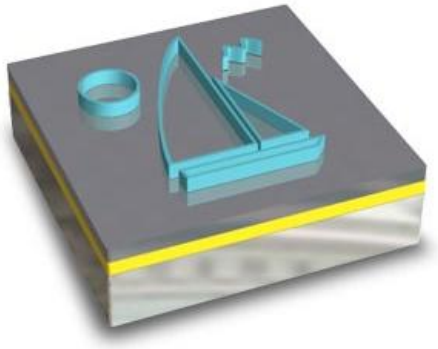
Photolithographic Process



A mask containing the pattern of the sailboat, the sun, and a seagull is then placed over the wafer and ultraviolet light is then passed through the pattern exposing the soft photoresist beneath.

back forward

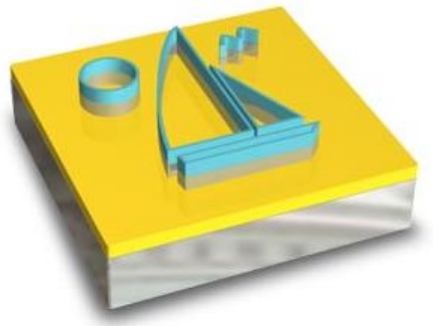
Photolithographic Process



The soft unexposed photoresist is removed with an organic solvent leaving only those areas that were hardened by exposure to the ultraviolet light. An outline of the seascape is now in place.

back forward

Photolithographic Process



The exposed areas of aluminum metal are now removed by "etching" the surface of the wafer in a process called ion beam milling that removes the unprotected aluminum.

back forward

Photolithographic Process

The hardened photoresist is then removed by washing with acid and the seascape is finished. We can now photograph it through a microscope and add it to the gallery in the Silicon Zoo.

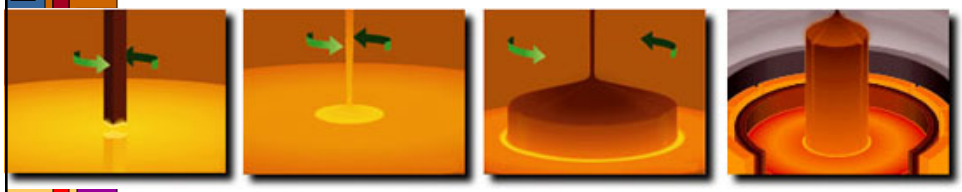
back

Growing the Silicon Crystal

Single Crystal Silicon Ingot

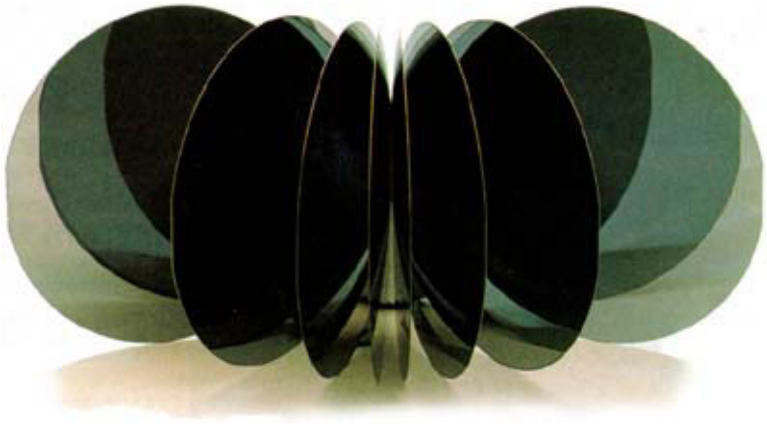
- Need single crystal structure
  - Single crystal vs. Polycrystalline silicon (Poly)

Czochralski Method



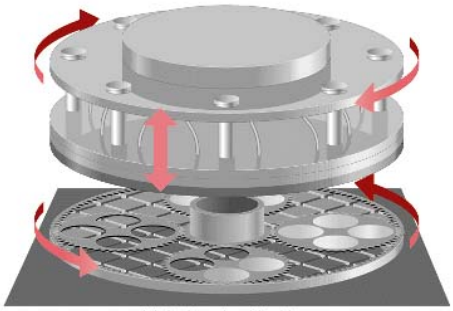
- Need single-crystal silicon to accept impurities correctly
  - Donor elements provide electrons
  - Acceptor elements provide holes
- Pull a single crystal of silicon from a puddle of molten polycrystalline silicon

Slice Crystal into Wafers



- Slice into thin wafers (.25mm - 1.0mm), and polish to remove all scratches

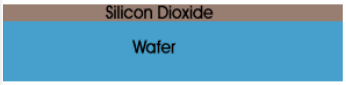
Lapping and Polishing



Wafer Polishing
(Strasbaugh Corporation)

Oxidation, Growing SiO2

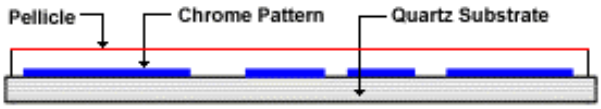
Oxidation Furnace
(Silicon Valley Group - Thermco Systems)



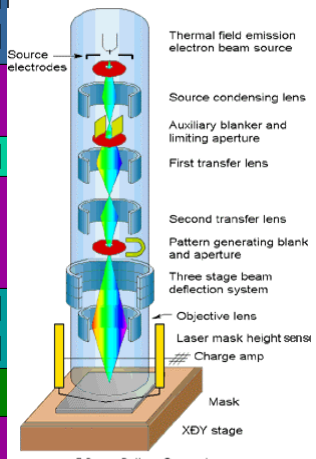
Oxidation Layering

- Essential property of silicon is a nice, easily grown, insulating layer of SiO2
  - Use for insulating gates (“thin oxide”)
  - Also for “field oxide” to isolate devices

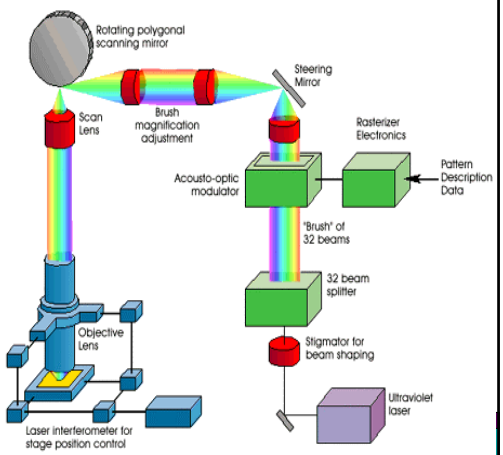
Making the Mask



Reticle



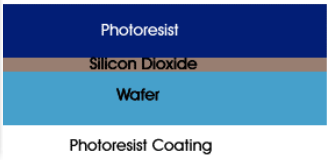
E-Beam Pattern Generator
(Etec Corporation)



Laser Pattern Generator (Etec Corporation)

Adding Photoresist

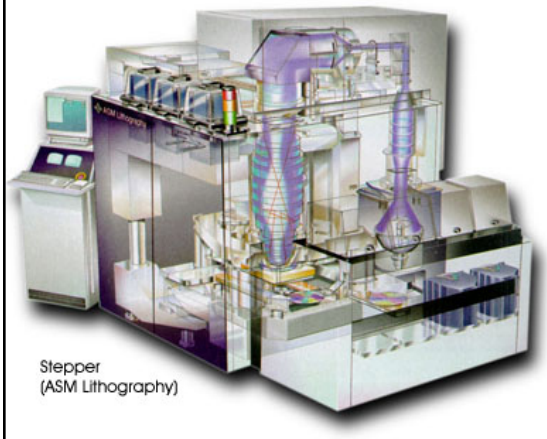
Photoresist Application
(Ontrak)



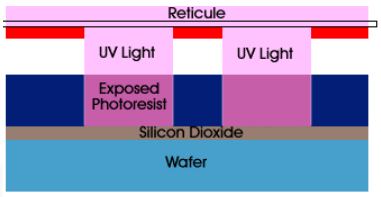
Photoresist Coating

- Photoresist can be positive or negative
  - Does the exposed part turn hard, or the unexposed part?

"Steppers" Expose the Mask



Stepper
(ASM Lithography)

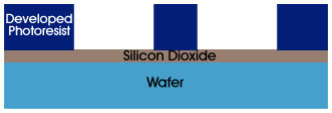


Exposure

- Use very short wavelength UV light
  - Single frequency, 436 - 248 nm
- Expensive! ~$5,000,000/machine…

Develop and Bake Photoresist

Oxidation Furnace
(Silicon Valley Group - Thermco Systems)

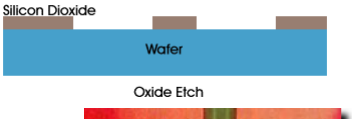


Photoresist Develop & Strip

- Developed photoresist is soft, unexposed is hardened
  - So you can etch away the soft (exposed) part

Now Etch the SiO2

Automated Acid Etch
(SEZ)



Oxide Etch

SRD (Spin, Rinse, Dryer)
(SEZ)

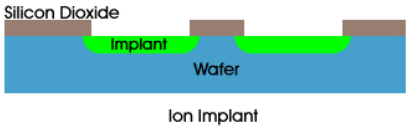
- Etch the SiO2 to expose the wafer for processing
- Then Spin Rinse, and Dry

Add a Processing Step

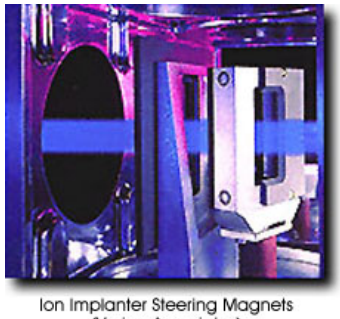
- Now that we've got a pattern etched to the right level, we can process the silicon
- Could be:
  - Ion Implantation (I.e. diffusion)
  - Chemical Vapor Deposition (silicide, Poly, insulating layers, etc.)
  - Metal deposition (evaporation or sputtering)
  - Copper deposition (very tricky)

Ion Implantation

Ion Implanter
(Varian Associates)



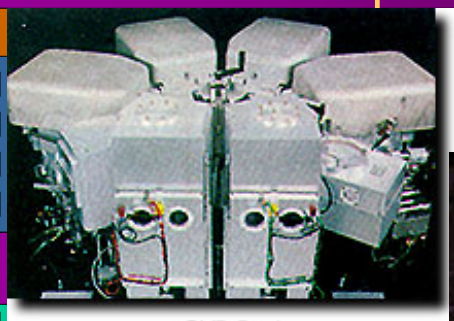
Ion Implant



Ion Implanter Steering Magnets
(Varian Associates)

- Implant ions into the silicon
  - Donor or Acceptor

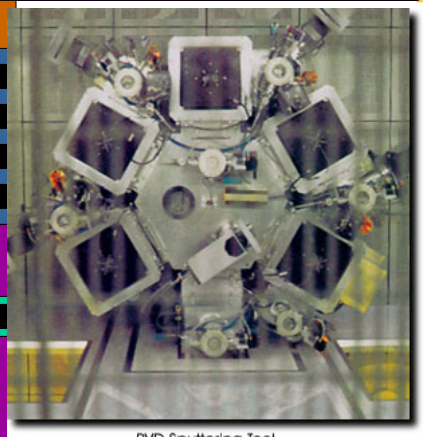
Chemical Vapor Deposition



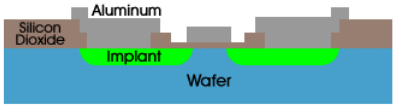
CVD Tool
(Applied Materials)

CVD Tool
(Applied Materials)

Metal Deposition



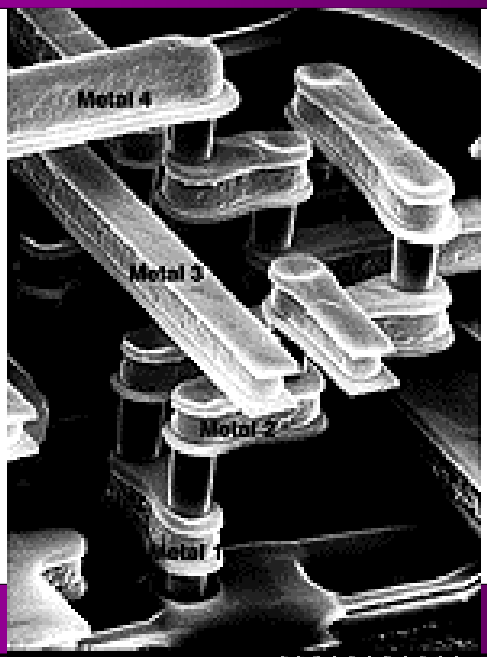
PVD Sputtering Tool
(Sputtered Films Corporation)



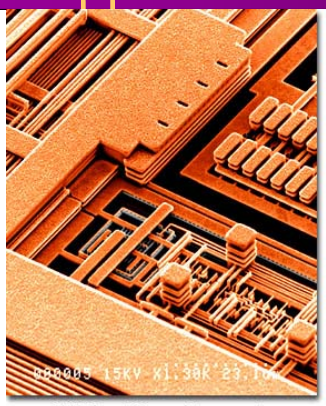
Metal Deposition

- Typically aluminum, gold, tungsten, or alloys

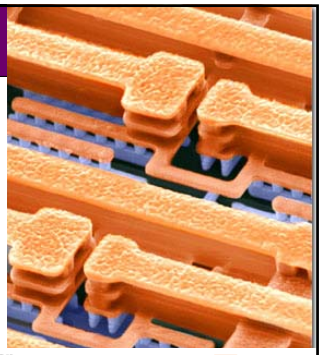
Advanced Metalization



Copper is Tricky



SEM view of Copper Interconnect
(IBM Microelectronics)

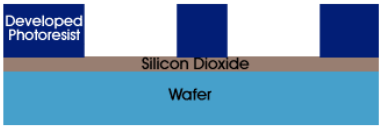


Copper Deposition

- 40% less resistance than Aluminum
  - 15% system speed increase
- But, copper diffuses into Silicon and changes the electrical properties

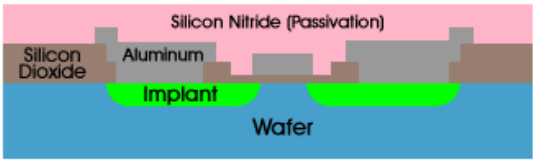
Ashing - Removing Photoresist

Plasma Asher
(Fusion Systems)



Photoresist Develop & Strip

Final Layer: Passivation



Passivation

- Basically a final insulating layer (SiO2 or Si3N4) to protect the circuit

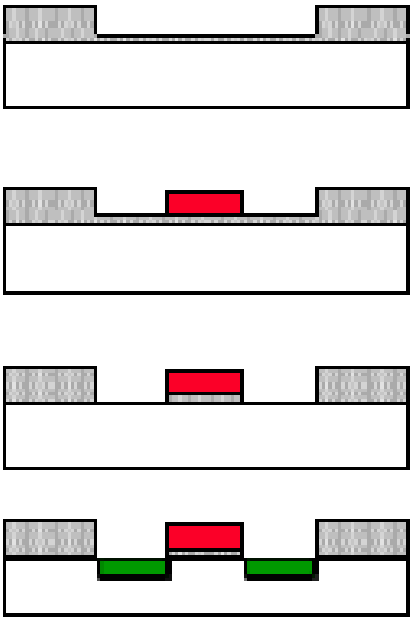
CMOS Fabrication

- Start from single-crystal silicon wafer
- Use photolithography to pattern device layers
  - Essentially one mask/photolithographic sequence per layer
  - Built (roughly) from the bottom up
    - 6 - Metal 3
    - 5 - Metal 2
    - 4 - Metal 1
    - 2 - Polysilicon
    - 3 - Diffusions
    - 1 Tub (N-well)

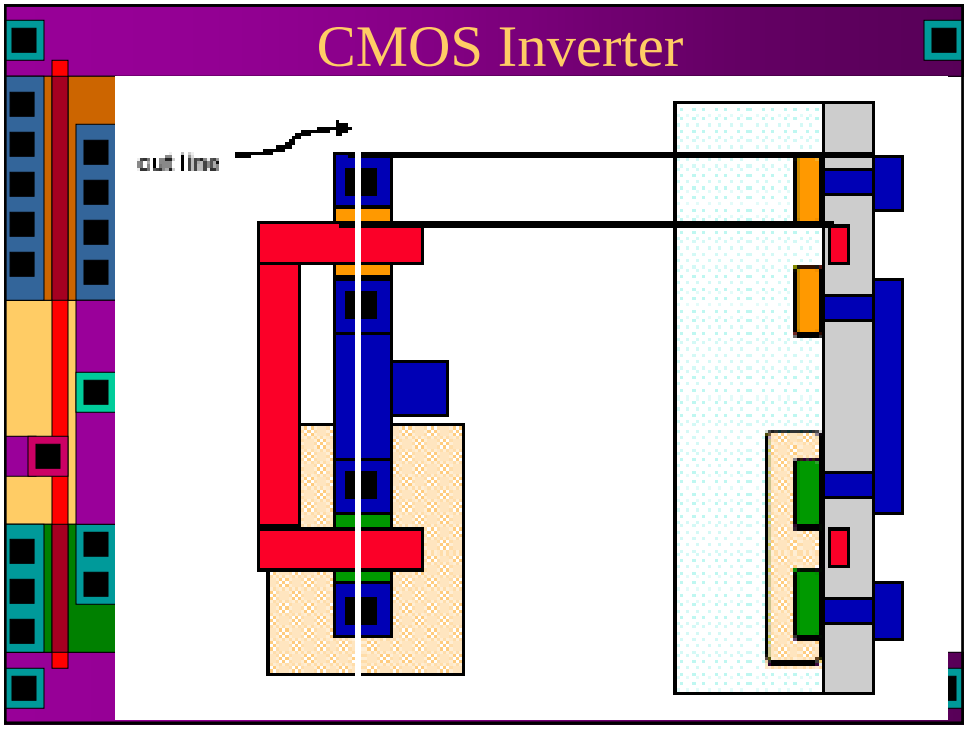
Via
Via
Contact
Exception

Self-Aligned Gates

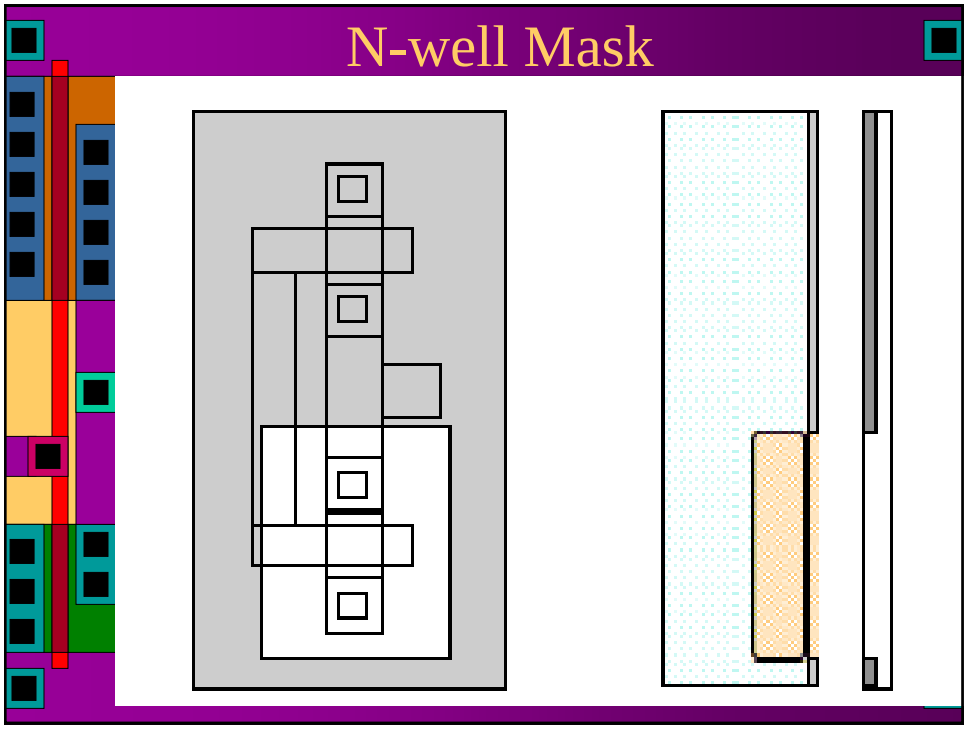
- Thinox in active regions, thick elsewhere
- Deposit Polysilicon
- Etch thinox from active region (Poly serves as mask for etch/diffusion)
- Implant dopant

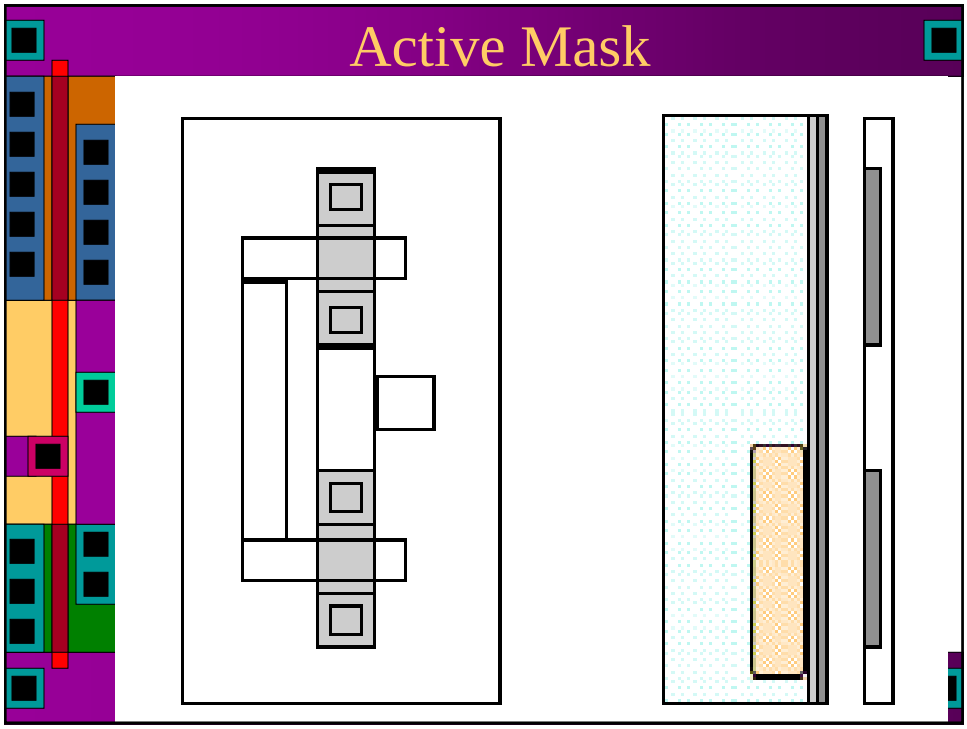


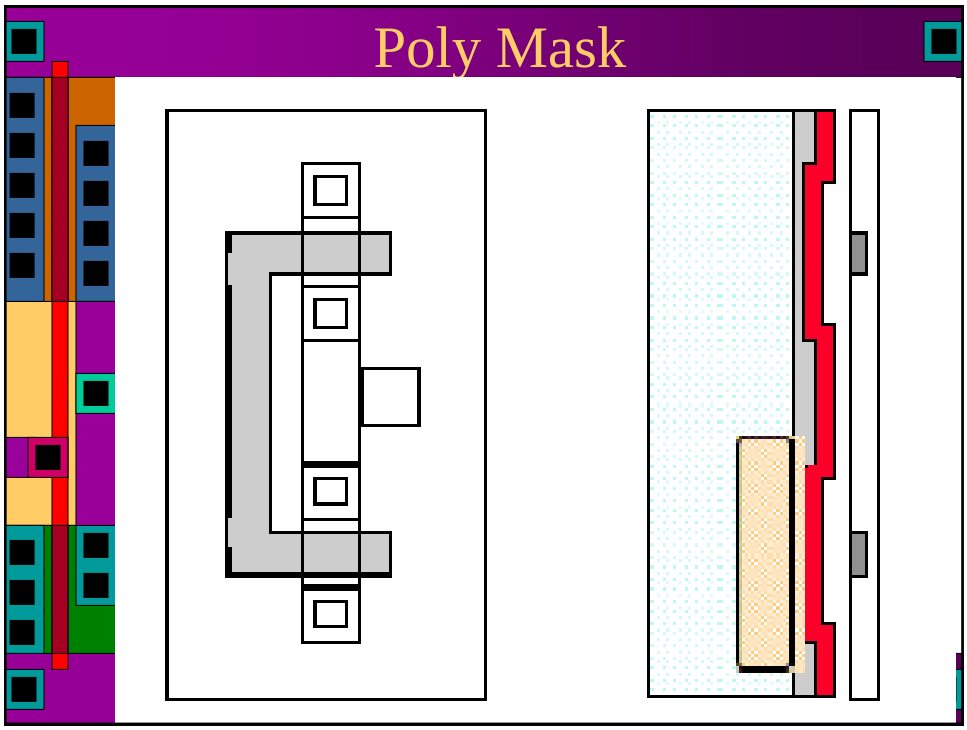
CMOS Inverter

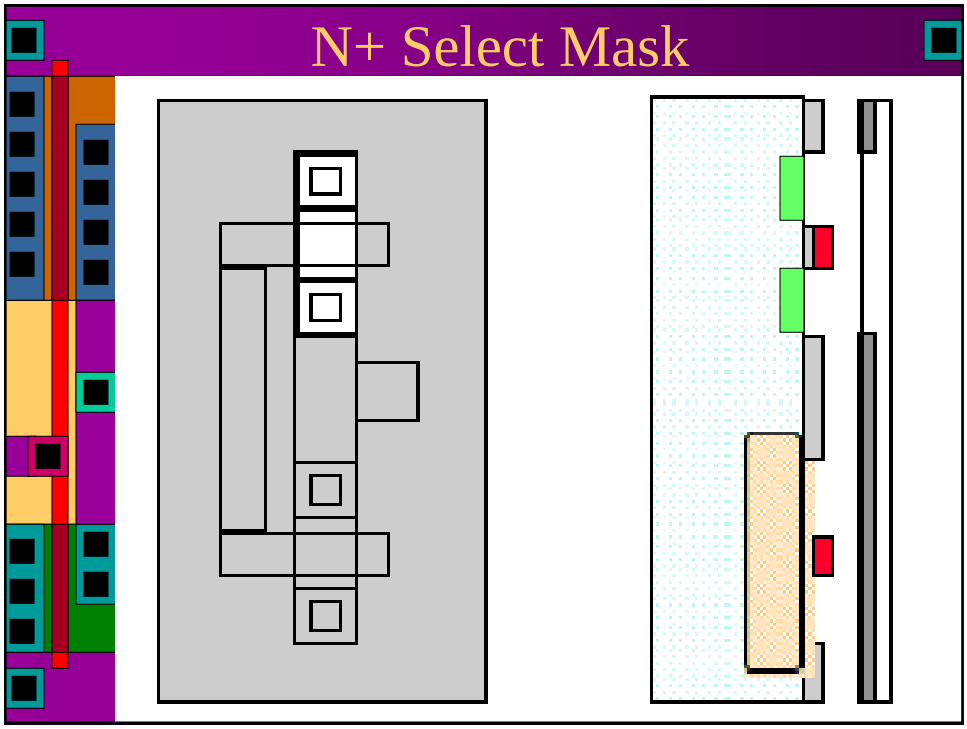


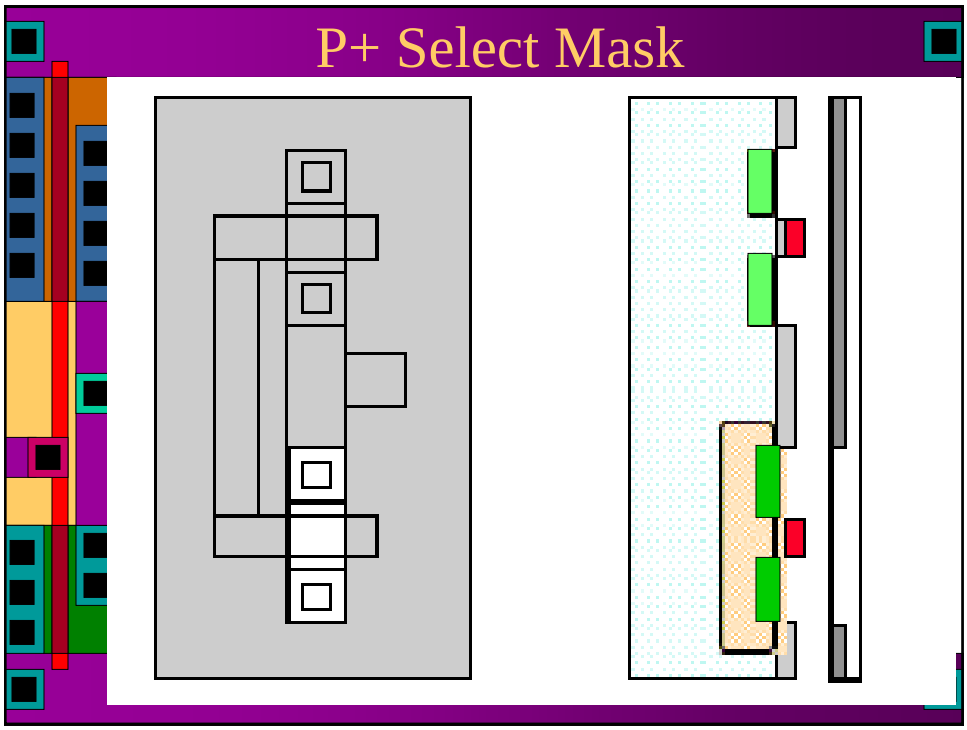
N-well Mask

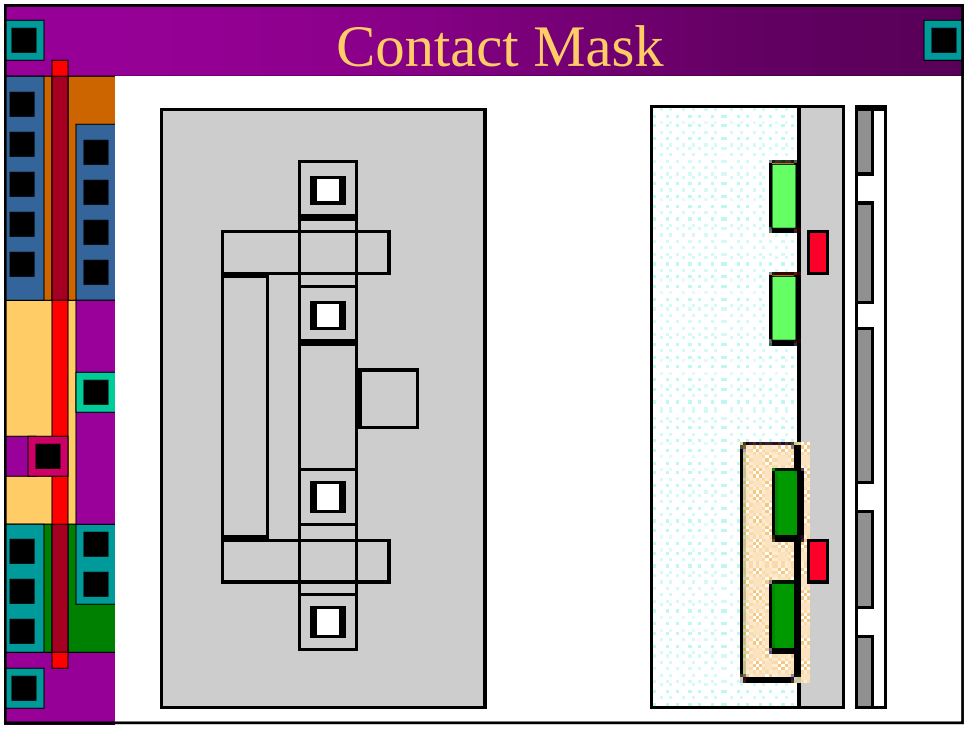


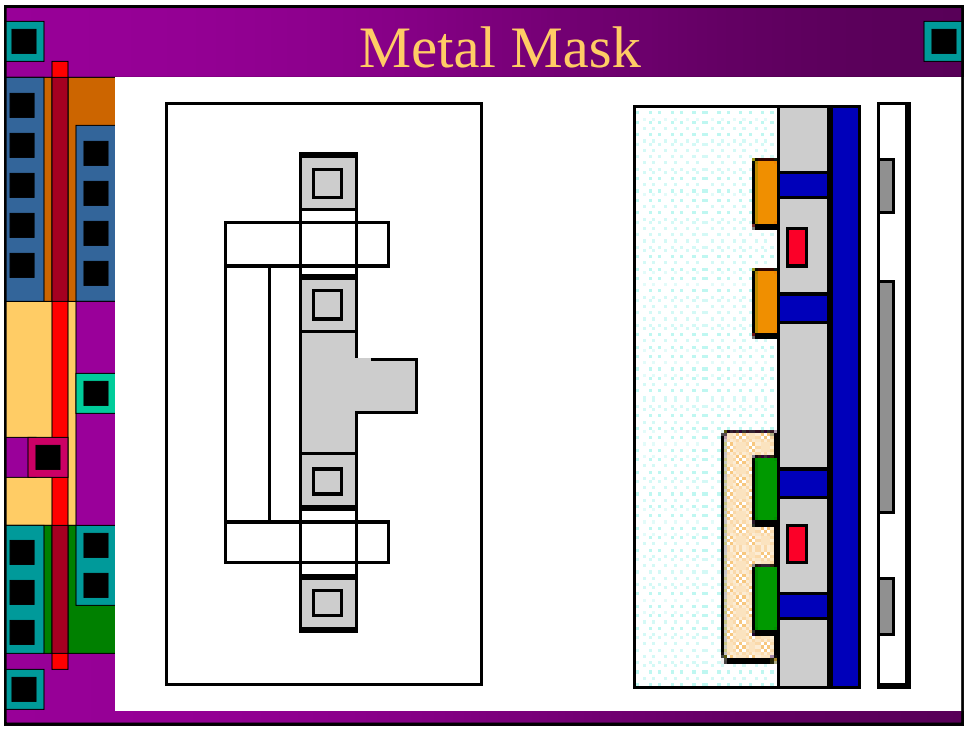

Active Mask


Poly Mask

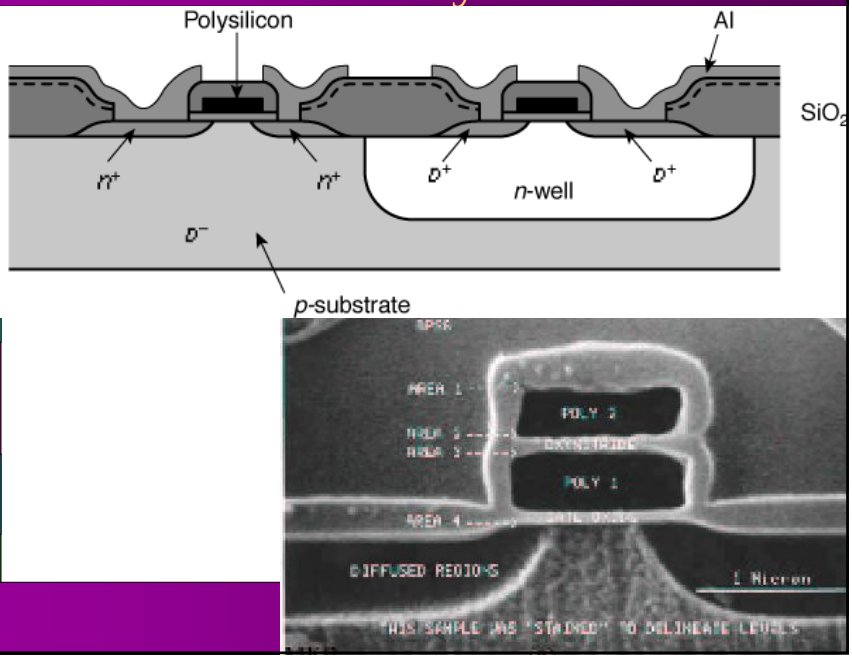

N+ Select Mask


P+ Select Mask


Contact Mask

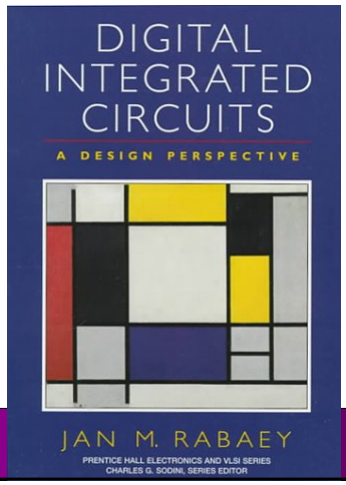

Metal Mask

Other Cutaway Views

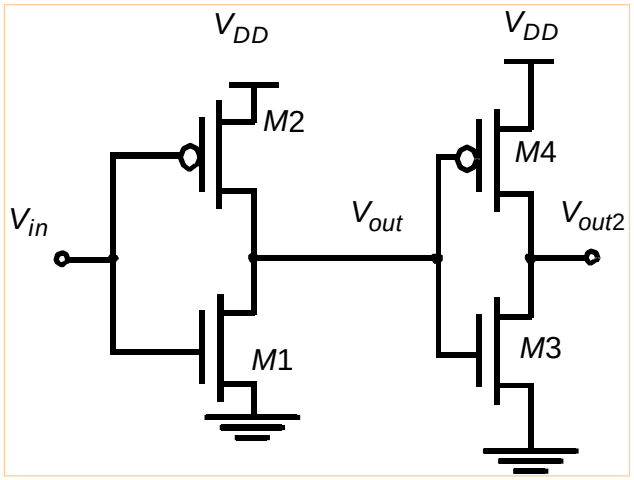


Another View of Fab

- Taken from slides by Jan Rabaey
  - From his text “Digital Integrated Circuits”

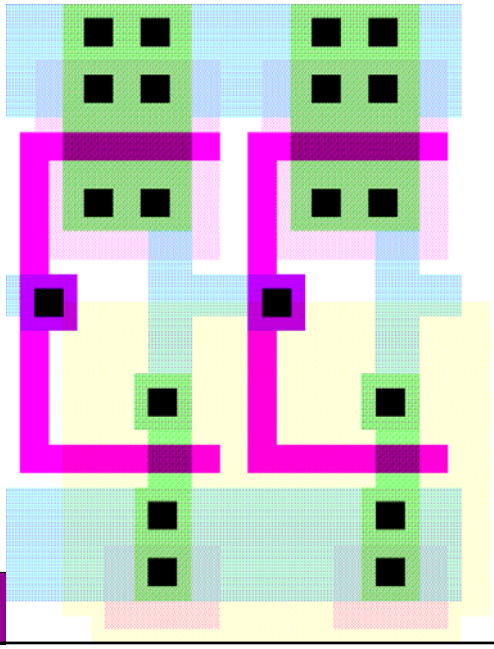


Circuit Under Design

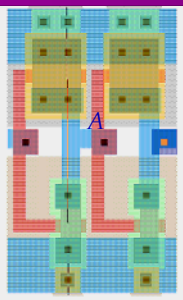


This two-inverter circuit (of Figure 3.25 in Rabaey's text) will be manufactured in a twin-well process.

Circuit Layout



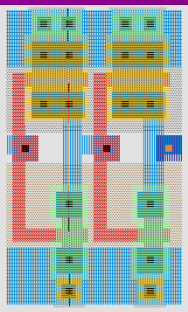
Start Material



Starting wafer: n-type with doping level = $10^{13}/cm^3$

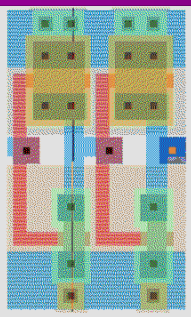
* Cross-sections will be shown along vertical line ***A-A'***

N-well Construction



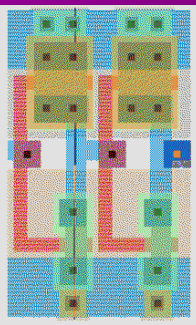
(1) Oxidize wafer
(2) Deposit silicon nitride
(3) Deposit photoresist

N-well Construction



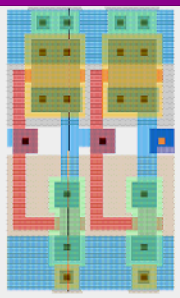
(4) Expose resist using n-well mask

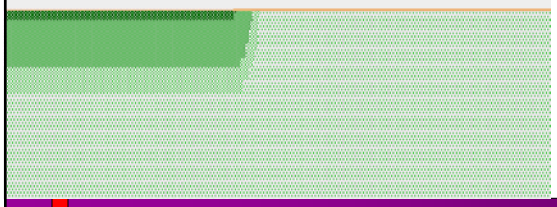
N-well Construction



(5) Develop resist
(6) Etch nitride and
(7) Grow thick oxide

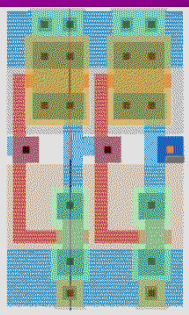
N-well Construction

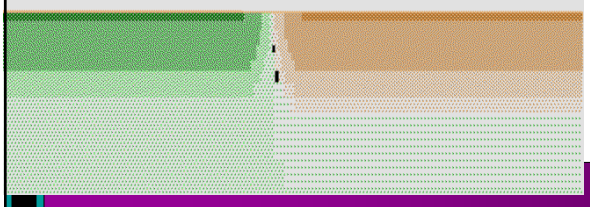




(8) Implant n-dopants (phosphorus) (up to 1.5 μm deep)

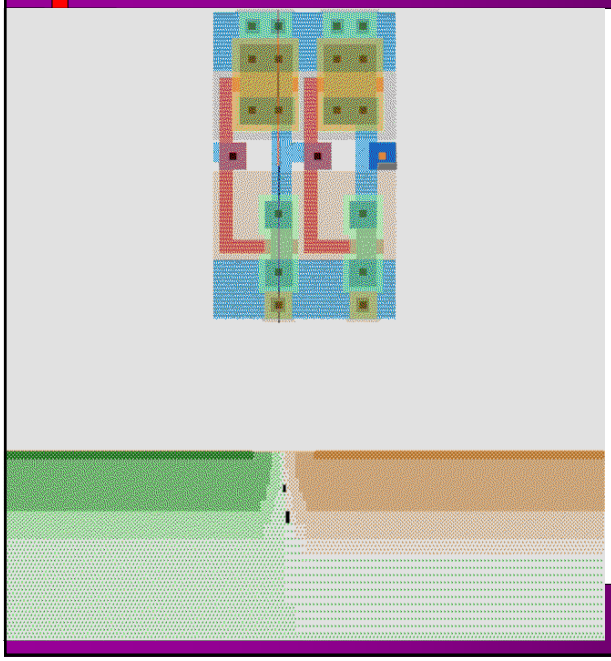
P-well Construction





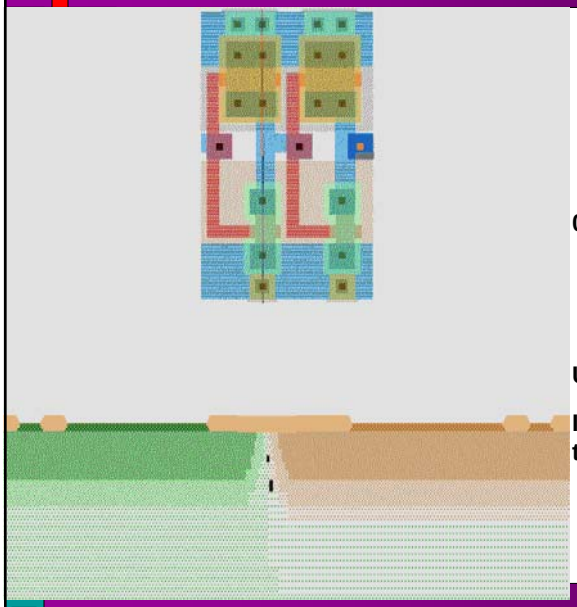
Repeat previous steps

Grow Gate Oxide



0.055 μm thin

Grow Thick Field Oxide

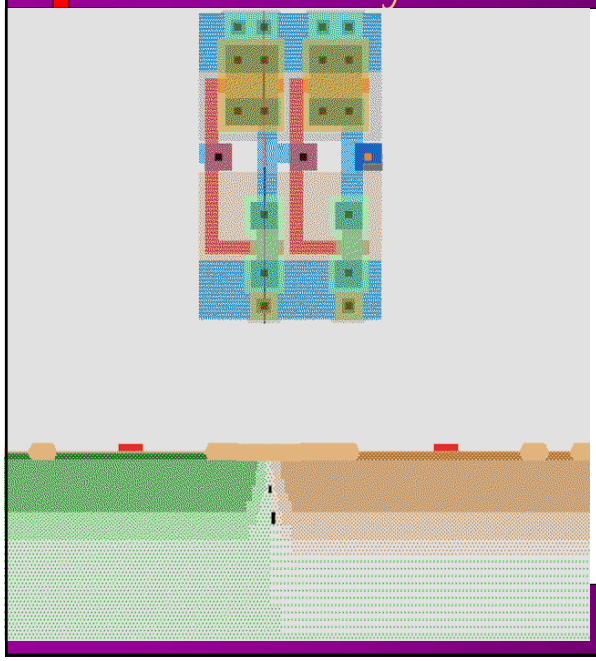


0.9 μm thick

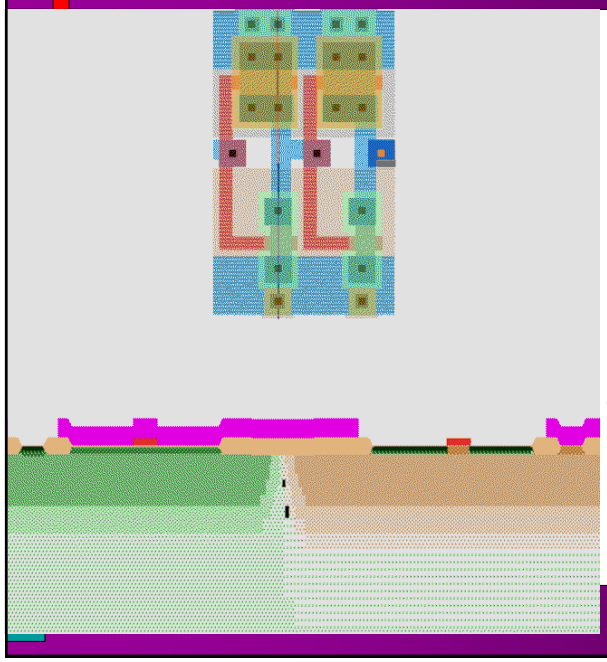
Uses Active Area mask

Is followed by threshold-adjusting implants

Polysilicon layer

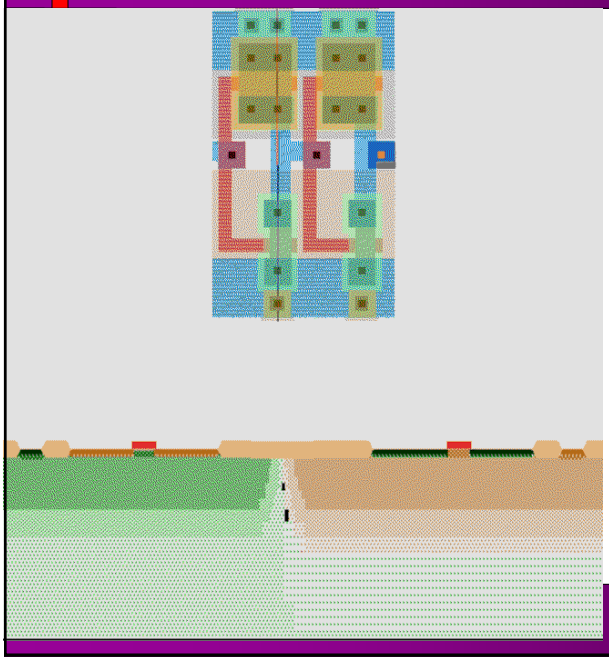


Source-Drain Implants



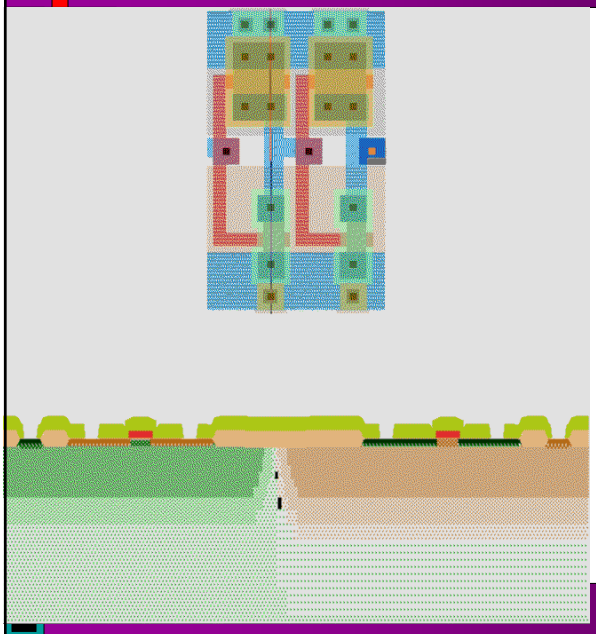
n+ source-drain implant
(using n+ select mask)

Source-Drain Implants



p+ source-drain implant
(using p+ select mask)

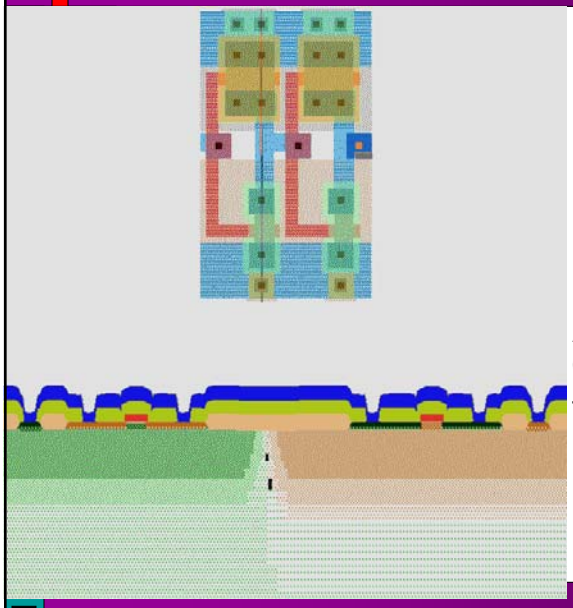
Contact-Hole Definition



(1) Deposit inter-level dielectric (SiO_2) — 0.75 μm

(2) Define contact opening using contact mask

Aluminum-1 Layer



Aluminum evaporated (0.8 μm thick)

followed by other metal layers and glass